



#12B And.
M. Brunson
8/28/02
PATENT

Customer No. 22,852
Attorney Docket No. 04329.2222

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)

Kouji MATSUO, et al.)

Serial No.: 09/492,780)

Filed: January 28, 2000)

For: SEMICONDUCTOR DEVICE AND)
METHOD OF MANUFACTURING)
THE SAME)

Group Art Unit: 2814

Examiner: Rao, Shrinivas H.

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TECHNOLOGY CENTER 2800

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

AMENDMENT

In reply to the Final Office Action of May 31, 2002, and in support of the RCE filed concurrently herewith, please amend the application as follows:

IN THE CLAIMS:

Please amend claim 12 as follows:

12. (Twice Amended) A semiconductor device, comprising:

a semiconductor substrate;

a metal-containing insulating film formed directly or indirectly on said semiconductor substrate, said metal-containing insulating film including a plurality of first insulating regions each of which is formed of a grain containing a metal oxide and a second insulating region, said second insulating region formed of an amorphous insulating material; and

an electrode formed on said metal-containing insulating film.

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